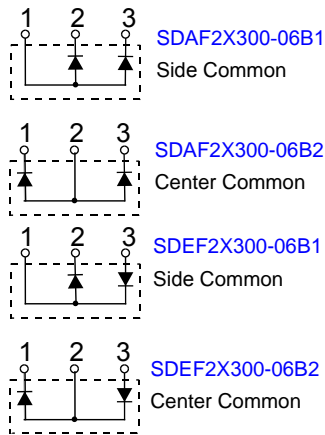
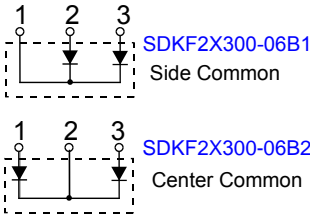
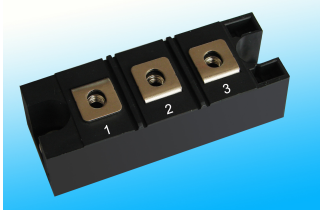
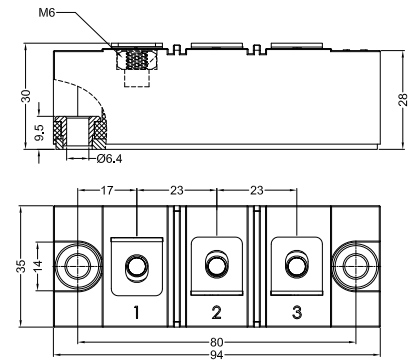


SDKF/SDAF/SDEF2x300-06B1/B2

Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules



Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions	Maximum Ratings	Unit
IFRMS	$T_C=75^\circ\text{C}$	430	A
IFAVM	$T_C=75^\circ\text{C}$; rectangular, $d=0.5$	2 x 300	
IFRM	$t_p < 10\mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	1640	
IFSM	$T_{VJ}=45^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	A
	$T_{VJ}=150^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	
I^2t	$T_{VJ}=45^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	A^2s
	$T_{VJ}=150^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+125	
T_{Smax}		110	
P_{tot}	$T_C=25^\circ\text{C}$	875	W
V_{ISOL}	50/60Hz, RMS $t=1\text{min}$	3000	V~
	$I_{\text{ISOL}} \leq 1\text{mA}$ $t=1\text{s}$	3600	
M_d	Mounting torque (M6)	2.25-2.75/20-25	Nm/lb.in.
	Terminal connection torque (M6)	4.50-5.50/40-48	
ds	Creeping distance on surface	12.7	mm
dA	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s^2
Weight		170	g



SDKF/SDAF/SDEF2x300-06B1/B2

Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I_R	$T_{VJ}=25^{\circ}\text{C}; V_R=V_{RRM}$		12	mA
	$T_{VJ}=25^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$		3	
	$T_{VJ}=125^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$		80	
V_F	$I_F=150\text{A}; T_{VJ}=125^{\circ}\text{C}$		1.05	V
	$T_{VJ}=25^{\circ}\text{C}$		1.27	
	$I_F=260\text{A}; T_{VJ}=125^{\circ}\text{C}$		1.19	
	$T_{VJ}=25^{\circ}\text{C}$		1.36	
V_{TO}	For power-loss calculations only		0.85	V
r_T			1.34	mΩ
R_{thJH} R_{thJC}	DC current DC current		0.228 0.143	K/W
t_{rr} I_{RM}	$I_F=300\text{A}; T_{VJ}=100^{\circ}\text{C}$ $V_R=300\text{V}; T_{VJ}=25^{\circ}\text{C}$ $-di/dt=400\text{A}/\mu\text{s}; T_{VJ}=100^{\circ}\text{C}$	250	300 44 66	ns A A

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Short recovery time
- * Low switching losses
- * Soft recovery behaviour
- * Isolation voltage 3600 V~
- * RoHS compliant

APPLICATIONS

- * Antiparallel diode for high frequency switching devices
- * Free wheeling diode in converters and motor control circuits
- * Inductive heating and melting
- * Uninterruptible power supplies (UPS)
- * Ultrasonic cleaners and welders

ADVANTAGES

- * High reliability circuit operation
- * Low voltage peaks for reduced protection circuits
- * Low noise switching
- * Low losses

Sirectifier®

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Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules

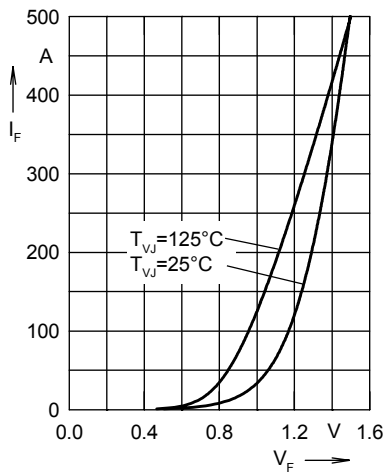


Fig. 1 Forward current I_F versus max. voltage drop V_F per leg

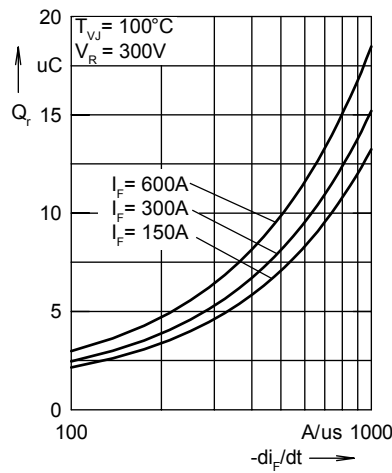


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

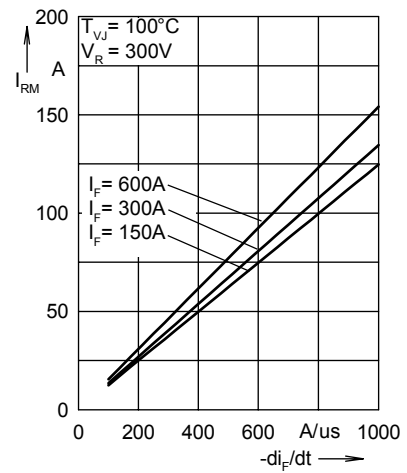


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

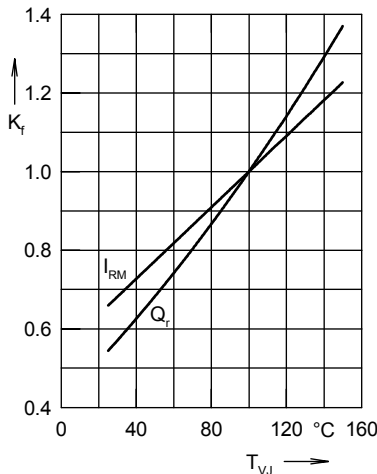


Fig. 4 Dynamic parameters Q_r , I_{RM} versus junction temperature T_{VJ}

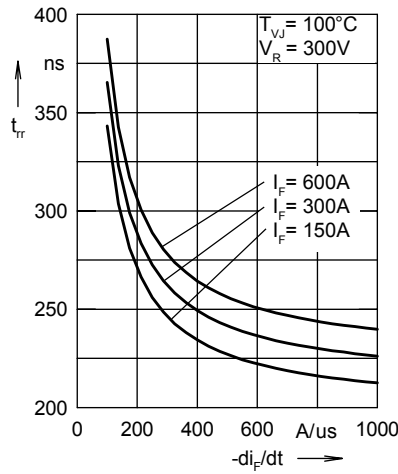


Fig. 5 Typ. recovery time t_{tr} versus $-di_F/dt$

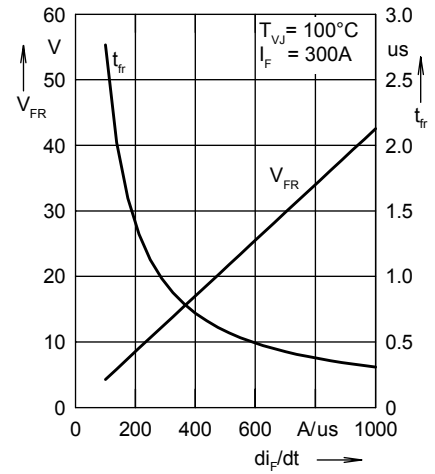


Fig. 6 Typ. peak forward voltage V_{FR} and t_{tr} versus di_F/dt

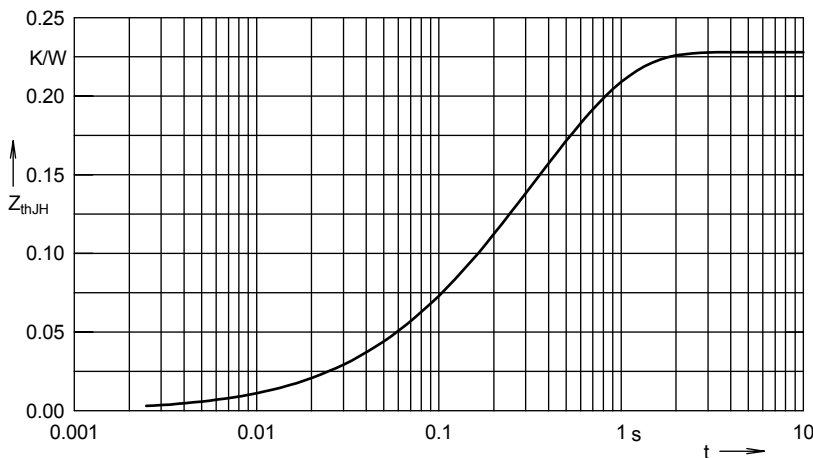


Fig. 7 Transient thermal impedance junction to heatsink

Constants for Z_{thJS} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.002	0.08
2	0.008	0.024
3	0.054	0.112
4	0.164	0.464

